



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

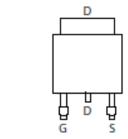
BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
	15mΩ @ V _{GS} = 10V	52.7A
100V	18mΩ @ V _{GS} = 6V	48A
	25mΩ @ V _{GS} = 4.5V	40A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting



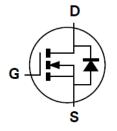


Features

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Equivalent Circuit

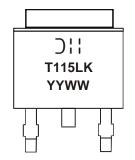
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H015LK3-13	TO252 (DPAK)	2.500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Oll = Manufacturer's Marking
T115LK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	100	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		I _D	52.7 42.1	А
Pulsed Drain Current (10μs Pulse, T _C = +25°C, Package Limited)	I _{DM}	210	A	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	48	A
Pulsed Body Diode Forward Current (10μs Pulse, T _C = +25°C, Package Limited)		I _{SM}	210	A
Avalanche Current, L = 3mH		I _{AS}	7.5	A
Avalanche Energy, L = 3mH		E _{AS}	85	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	69	°C/W
Total Power Dissipation (Note 6)		P _D	2.9	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	2	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

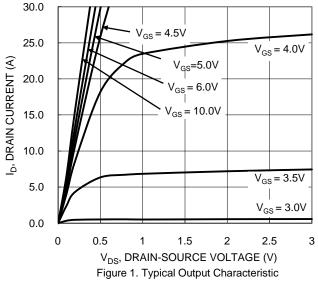
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

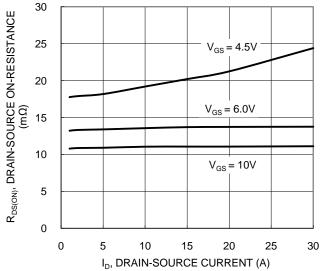
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100		_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	I	I	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.4	1	3.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		I	10.7	15		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	13.1	18	$m\Omega$	$V_{GS} = 6V, I_D = 20A$	
		_	18.2	25		$V_{GS} = 4.5V, I_D = 5A$	
Diode Forward Voltage	V_{SD}	I	I	1.3	٧	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	CISS	1	1871	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	261	_	pF		
Reverse Transfer Capacitance	C _{RSS}	1	6.9	_		1 - 1101112	
Gate Resistance	Rg		0.75	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{G}	1	33.3	_		V 50V L 40A	
Gate-Source Charge	Q_{GS}		6.9	_	nC	$V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_GD	l	5.1	_			
Turn-On Delay Time	t _{D(ON)}		6.5	_			
Turn-On Rise Time	t _R	_	7.0	_	ns	$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 10A, R_{G} = 6\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	19.7	_	115		
Turn-Off Fall Time	t _F	1	8.1	_			
Reverse Recovery Time	t _{RR}	_	37.9	_	ns L 404 divite 4004 / co		
Reverse Recovery Charge	Q _{RR}	_	51.9	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

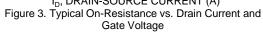
Notes:

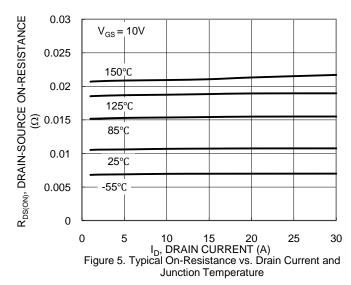
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

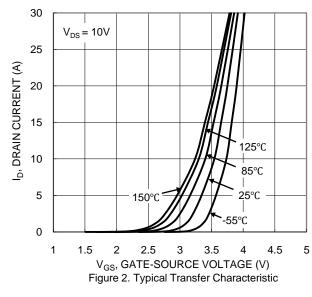


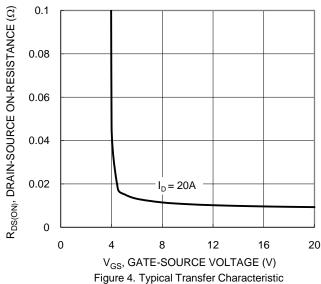


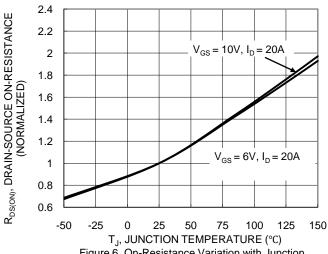






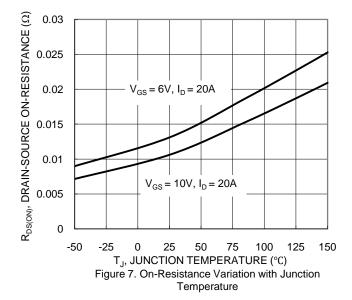


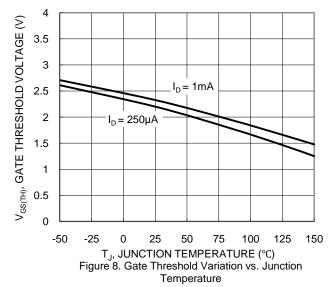


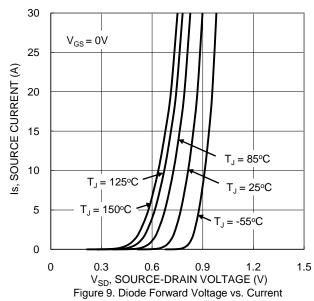


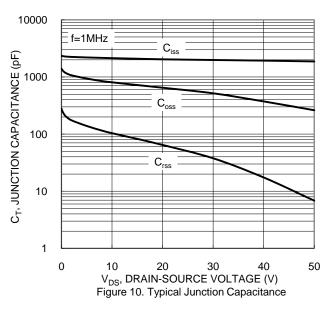


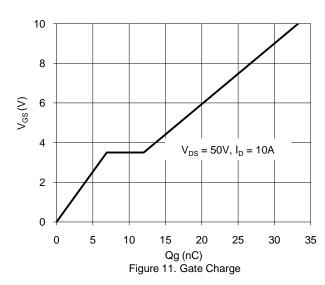


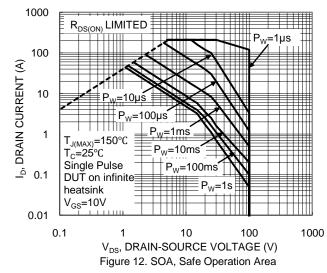














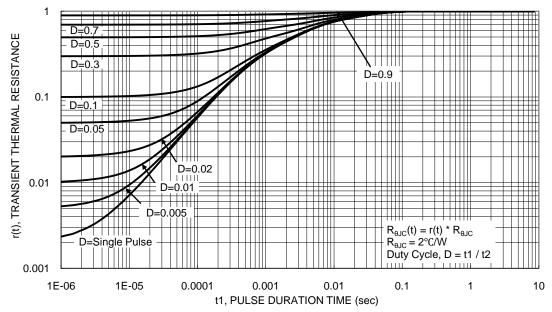


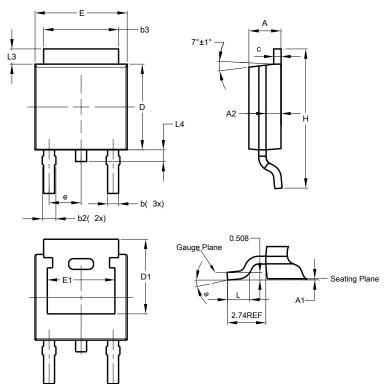
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

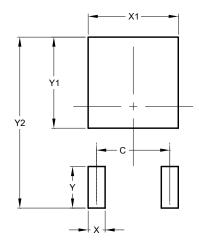


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
p	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
П	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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